

# RGCL80TK60

### 600V 40A Field Stop Trench IGBT

V <sub>CES</sub>	600V
I <sub>C(100°C)</sub>	21A
V <sub>CE(sat) (Typ.)</sub>	1.4V@I <sub>C</sub> =40A
$P_D$	57W

#### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Soft Switching
- 3) Pb free Lead Plating; RoHS Compliant

#### Applications

Partial Switching PFC

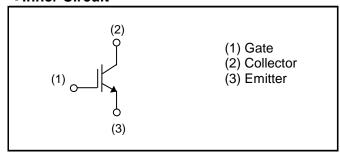
Discharge Circuit

Brake for Inverter

#### Outline



#### ●Inner Circuit



Packaging Specifications

	Packaging	Tube		
		Reel Size (mm)	-	
١,	Tuno.	Tape Width (mm)	-	
	Гуре	Basic Ordering Unit (pcs)	450	
		Packing Code	C11	
		Marking	RGCL80TK60	

### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	600	V
Gate - Emitter Voltage		$V_{GES}$	±30	V
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	600 ±30 35 21 160 57 28	А
Collector Current	T <sub>C</sub> = 100°C	I <sub>C</sub>	21	А
Pulsed Collector Current	urrent		160	А
Dower Dissipation	$T_{C} = 25^{\circ}C$ $T_{C} = 100^{\circ}C$ $T_{C} = 25^{\circ}C$ $T_{C} = 100^{\circ}C$	P <sub>D</sub>	57	W
Power Dissipation	T <sub>C</sub> = 100°C	P <sub>D</sub>	28	W
Operating Junction Temperatur	perating Junction Temperature		-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>imax.</sub>

#### ●Thermal Resistance

Darameter	Symbol	Values			Unit
Parameter		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	2.62	°C/W

# ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
raiainetei	Syllibol		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	600	1	1	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 600V, V_{GE} = 0V$	ı	1	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V$ , $V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 30.0 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 40A$ , $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C		1.4 1.6	1.8	V

# ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Doromotor	Symbol	Conditions	Values			Lloit
Parameter			Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	2340	-	
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V$	-	55	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	43	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 300V	-	98	-	
Gate - Emitter Charge	$Q_{ge}$	I <sub>C</sub> = 40A	-	20	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	38	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 40A, V_{CC} = 400V$	-	53	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	34	-	no
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 25°C	-	227	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	204	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> includes diode	-	1.11	-	
Turn - off Switching Loss	E <sub>off</sub>	reverse recovery	-	1.68	-	mJ
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 40A, V_{CC} = 400V$	-	48	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_{G} = 10\Omega$	-	66	-	no
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 175°C	-	255	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	310	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> includes diode	-	1.51	-	
Turn - off Switching Loss	E <sub>off</sub>	reverse recovery	-	2.30	-	mJ
		$I_C = 160A, V_{CC} = 480V$				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 600V, V_{GE} = 15V$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Fig.1 Power Dissipation vs. Case Temperature

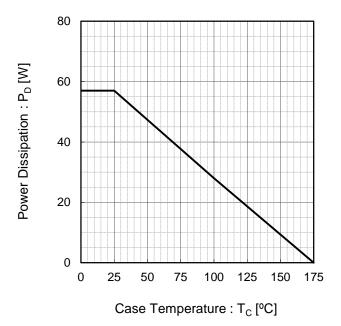


Fig.2 Collector Current vs. Case Temperature

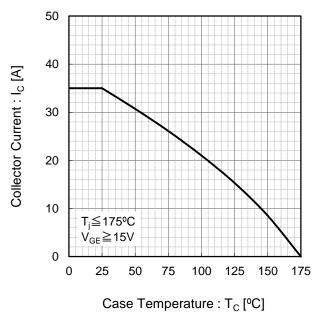


Fig.3 Forward Bias Safe Operating Area

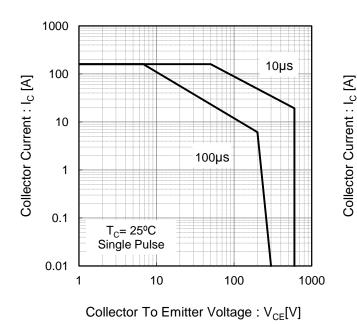
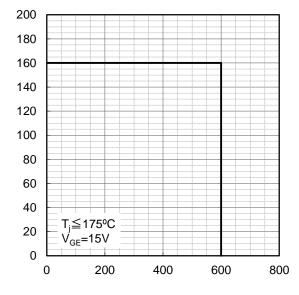


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.5 Typical Output Characteristics

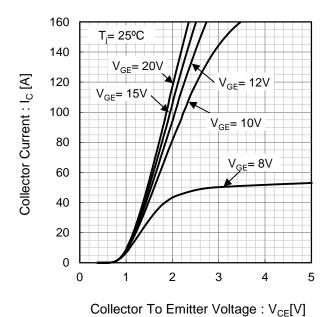
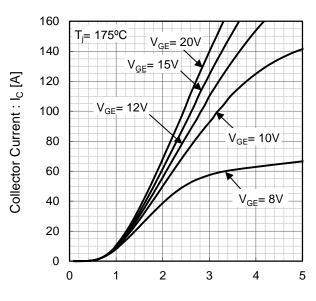
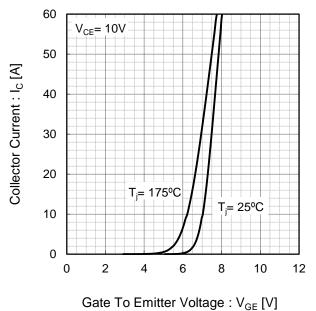


Fig.6 Typical Output Characteristics



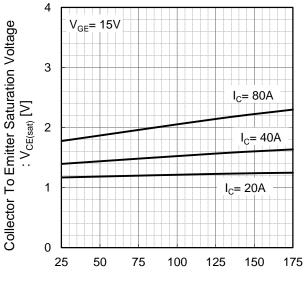
Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.7 Typical Transfer Characteristics



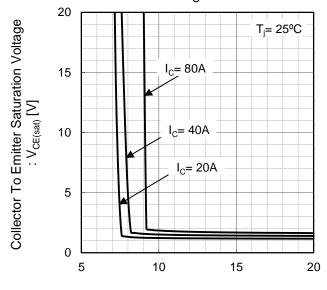
vs. Junction Temperature

Fig.8 Typical Collector To Emitter Saturation Voltage



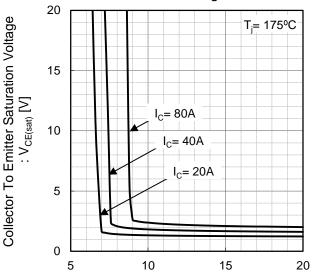
Junction Temperature : T<sub>i</sub> [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

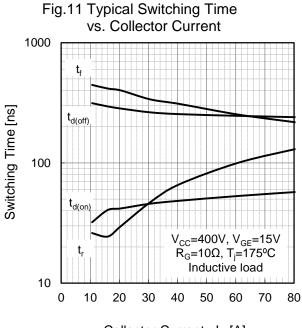


Gate To Emitter Voltage : V<sub>GE</sub> [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage: V<sub>GE</sub> [V]



Collector Current : I<sub>C</sub> [A]

Fig.12 Typical Switching Time vs. Gate Resistance 1000 Switching Time [ns]  $t_{d(off)}$ 100 t<sub>d(on)</sub>  $V_{CC} = 400V, I_{C} = 40A$ V<sub>GE</sub>=15V, T<sub>i</sub>=175°C Inductive load 10 10 40 0 20 30 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1  $\mathsf{E}_{\mathsf{on}}$ 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V  $R_{G}$ =10 $\Omega$ ,  $T_{j}$ =175°C Inductive load 0.01 0 10 20 30 40 50 60 70 80 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10  $\mathsf{E}_{\mathsf{off}}$ Switching Energy Losses [mJ] 1 Eon 0.1  $V_{CC}$ =400V,  $I_{C}$ =40A  $V_{GE}$ =15V,  $T_{j}$ =175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] 100 Coes Cres 10 f=1MHz V<sub>GE</sub>=0V T;=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]

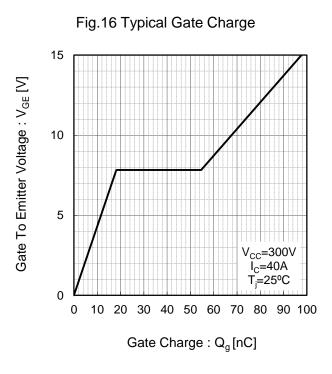
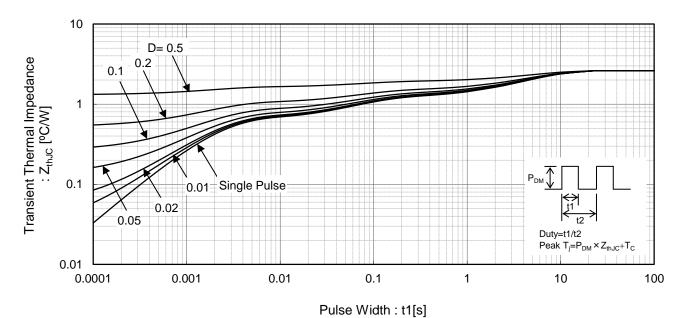


Fig.17 IGBT Transient Thermal Impedance



## ●Inductive Load Switching Circuit and Waveform

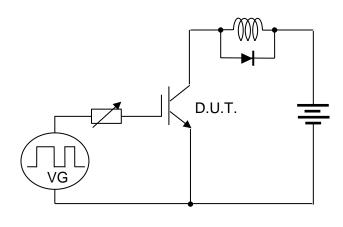


Fig.18 Inductive Load Circuit

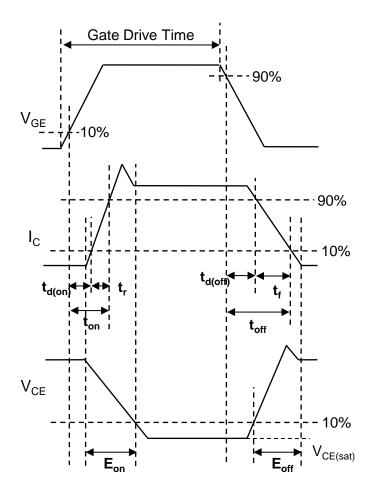


Fig.19 Inductive Load Waveform

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